Charge transport and phase transition in exciton rings

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The macroscopic exciton rings observed in the photoluminescence (PL) patterns of excitons in coupled quantum wells (CQWs) are explained by a series of experiments and a theory based on the idea of carrier imbalance, transport and recombination. The rings are found to be a source of cold excitons with temperature close to that of the lattice. We explored states of excitons in the ring over a range of temperatures down to 380mK. These studies reveal a sharp, albeit continuous, second order phase transition to a low-temperature ordered exciton state, characterized by ring fragmentation into a periodic array of aggregates. An instability at the onset of degeneracy in the cold exciton system, due to stimulated exciton formation, is proposed as the transition mechanism.

Bound electron-hole pairs – excitons – are light Bose particles [1] with a mass comparable or smaller than that of the free electron. Since the quantum degeneracy temperature scales inversely with the mass, it is anticipated that Bose-Einstein condensation (BEC) of excitons [1] can be achieved at temperatures as much as six orders of magnitude larger than the microKelvin temperatures employed in atom condensation [2,3]. High quantum degeneracy temperatures and the possibility to control exciton density by laser photoexcitation makes the cold exciton gas a paradigm system for studies of collective states and many-body phenomena. As well as BEC [1], the cold exciton and electron-hole systems are expected to host a range of novel collective states, such as a BCS-like condensate [4], paired two-dimensional Laughlin liquid [5], coupled Wigner solids [5], and an excitonic charge density wave state [6].

The theoretical predictions above rely on the experimental realization of cold exciton gases. Although the semiconductor crystal lattice can be routinely cooled to temperatures well below 1K in He-refrigerators, after decades of effort with various materials, it appears to be experimentally challenging to lower the temperature of the exciton gas to even a few Kelvins. The exciton temperature, T_X, determined by the ratio of the energy relaxation and recombination rates, exceeds by far the lattice temperature in most semiconductors. For T_X to approach the lattice temperature, the lifetime of excitons should considerably exceed their energy relaxation time.

Due to the long lifetime and high cooling rate, the indirect excitons in CQWs form a unique system in which a cold exciton gas can be created. The long lifetimes are due to spatial separation of the electron and hole wells [7] while high cooling rates result from momentum conservation being relaxed in the direction perpendicular to the QW plane [8]. The form of interaction is crucial for the formation of collective exciton states. In the absence of in-plane forces, the indirect excitons are dipoles oriented perpendicular to the QW plane. The repulsive interaction between such dipoles stabilizes the exciton state against the formation of metallic electron-hole droplets [5,9] and results in screening of in-plane disorder [10].

The seemingly unique opportunity to realize a cold exciton gas stimulated great interest and has led to active experimental studies [11,12,13,14,15,16,17,18,19]. Recently, an intriguing observation was made of bright macroscopic exciton rings in the spatial PL patterns in CQWs with an onset of fragmentation of the external ring into an ordered array of aggregates taking place at a few Kelvin [17]. Luminescence rings were also observed in other CQW materials [19]. Yet neither the rings nor their fragmentation have been accounted for by theory.

Here, the conundrum of ring formation is resolved by new experiments, leading to a consistent and compelling picture, based on the mechanism of carrier imbalance, transport and recombination. We conclude that, since the carriers recombining to form the excitons are in thermal equilibrium, the rings represent a source of cold excitons. As such, the rings present a new opportunity to study novel states of the cold exciton gas.

With this motivation, we have explored states of excitons in the ring over a range of temperatures down to 380mK. These studies reveal a sharp, albeit continuous, second order phase transition to a low-temperature ordered exciton state. We present a phase diagram and propose a model for fragmentation involving hydrodynamical instability due to stimulated exciton formation at the onset of degeneracy in the exciton system.

The spatial distribution of indirect excitons, observed by measuring the PL pattern, undergoes a striking transformation as a function of photoexcitation power, P_{ex}. While at low P_{ex} the indirect excitons are observed only within the excitation spot, at high P_{ex} the most prominent feature in the PL pattern is a **bright ring** con-

centric with the laser spot and separated from it by an annular dark region (Fig. 1). The radius of the ring, and hence of the dark region, increases with P_{ex} [17] exceeding 100 μm at the highest intensities (Fig. 1a-c).

How can excitons appear so far away from the excitation spot? The excitons can, in principle, travel in a dark state after having been excited, until slowed down to a velocity below photon emission threshold, where they can decay radiatively [20]. This mechanism can account for the somewhat more diffuse inner ring of smaller radius up to tens of microns observed around the excitation spot [17]. However, within this framework, a number of qualitative features of the external ring appear to be difficult to explain. In particular — why the observed rings are so sharp, why the ring radius changes with the gate voltage, and why the rings produced by distant sources interact before overlapping.

To that end, we are led to assume that the excitons *are generated* within the ring. Indeed a general off-resonance laser excitation creates charge imbalance in the CQW structure, leading to carrier transport and recombination at large distances [21]. Most of the hot electrons and holes, created by the off-resonance excitation [17], cool down and form excitons giving rise to PL observed within or near the laser spot. However, charge neutrality of the carriers excited in CQW is generally violated mainly due to electrons and holes having different collection efficiency to the CQW. Overall charge neutrality in the sample is maintained by opposite charge accumulating in the doped region outside CQW. We note parenthetically that the sign of carrier imbalance cannot be deduced from first principles. We speculate that the current through CQWs from n-doped GaAs layers (Fig. 1f) creates electron gas in the CQW, while excess holes are photogenerated in the laser excitation spot. However, nothing in the discussion and conclusions below will be affected if electrons are replaced by holes and vice versa.

The holes created at the excitation spot diffuse out and bind with electrons, forming indirect excitons. This process depletes electrons in the vicinity of the laser spot, creating an essentially electron-free and hole rich region, which allows holes to travel a relatively large distance without encountering electrons. At the same time, a spatial nonuniformity of electron distribution builds up, causing a counterflow of electrons towards the laser spot. A sharp interface between the hole rich region and the outer electron rich area forms (Fig. 1e), since a carrier crossing into a minority region quickly binds with an opposite carrier to form an exciton. (Recently, possible relation between charge imbalance of photoexcited carriers and PL ring patterns has been informally discussed also by I.V. Kukushkin and D. Snoke.)

To summarize our transport model, electrons and holes move in the CQW plane, each species in its own quantum well, governed by coupled diffusion equations

$$\dot{n} = D\Delta n - wnp + J(r), \quad \dot{p} = D'\Delta p - wnp + J'(r) \quad (1)$$

with $n(r)$, $p(r)$ the electron and hole concentration, D, D' the diffusion constants, and w the rate at which an electron and hole bind to form an exciton. The source term for holes is localized at the excitation spot, $J'(r) = P_{ex}\delta(r)$, while the electron source is spread out over the entire plane, $J(r) = I(r) - a(r)n(r)$, with $I(r)$ and $a(r)n(r)$ the currents in and out of CQW. The stationary solution of Eqs. (1), displayed in Fig. 1e, indeed shows a structure of two regions dominated by electrons and holes, and separated by a sharp interface where exciton density $n_x \propto np$ is peaked. The radius of the inner hole region, determined by the balance between the radial hole flux and electron counterflow from the periphery, increases with the excitation power, as in the experiment (Fig. 1a-c). Density variation across the electron-hole interface can be obtained from a 1D system of stationary equations, $Dn'' = wnp$, $D'p'' = wnp$, with the boundary conditions $Dn_{x\to+\infty} = cx$, $n_{x\to-\infty} = 0$, where c is particle flux normal to the interface and, by symmetry, $D'p(x) = Dn(-x)$. Interface width scales as $(DD'/wc)^{1/3}$, making the exciton ring width practically independent of its radius (cf. Fig. 1a-c).

The exciton ring can be externally controlled by gate voltage: it expands by a factor of two after reducing the voltage across the structure from $V_g = 1.3$V to $V_g = 1.262$V (Fig. 2h-j). This is just as one expects since a reduction of transverse electric field, and hence of the current $I(r)$, depletes electrons in CQWs, while holes in the inner region remain practically unaffected.

Experiments with two rings created by spatially separated laser spots (Fig. 2a-d) reveal the most intriguing prediction of the transport model: the carrier distribution is strongly perturbed not only inside, but also outside the ring. As the spots are brought closer, the rings attract one another, deform, and then open towards each other (Fig. 2a-c). This happens well before the rings merge into a common oval-shaped ring (Fig. 2d), suggesting the existence of "dark matter" outside the rings that mediates the interaction. In the transport model, which readily accounts for the attraction (Fig. 2e-g), this dark matter is just the electron flow outside each ring which is perturbed by the presence of another ring. Electrons in the area between the rings are depleted more strongly than at the same radial distance in other directions, which shifts the balance of carrier fluxes to the hole side. As a result, the electron-hole interface moves further out between the rings.

The configuration of the electron-hole interface in a stationary state can be easily obtained by noting that the time-independent Eqs.(1) yield Poisson equation $\Delta\Phi = J_{tot} \equiv J' - J$ for the linear combination of electron and hole densities $\Phi = Dn - D'p$. The solution

$$\Phi(\mathbf{r}) = -\frac{1}{2\pi}\int \ln|\mathbf{r} - \mathbf{r}'| J_{tot}(\mathbf{r}')d^2r' \quad (2)$$

describes hole density in the region $\Phi > 0$ and electron density in the region $\Phi < 0$. The interface is thus given by the contour line $\Phi = 0$. In particular, two hole sources of equal strength at $\mathbf{r} = \mathbf{r}_{1,2}$ give a family of Bernoulli lemniscata $|\mathbf{r} - \mathbf{r}_1| \times |\mathbf{r} - \mathbf{r}_2| = \text{const}$ (Fig. 2e-g).

By defocussing the source and illuminating a large area (Fig. 3), a striking new feature emerges which presents a further piece of compelling evidence for the proposed mechanism. In the indirect exciton PL pattern, around the localized spots, small rings appear which mirror the behavior of the outer ring. However, the rings *shrink* at increasing laser power, indicating that electron-hole contrast here is inverted. This suggests that the spots reflect pinholes in the CQW barriers, each representing a localized source of electrons embedded in the hole rich inner area. A model with a bright hole source and a weaker electron source (Eqs.(1),(2)), shows the same qualitative behavior (Fig. 3g). Increasing hole flux (via P_{ex}), as soon as the electron source is enveloped by the hole rich area, a ring forms around it and then starts to shrink.

The most surprising feature of the spatial PL pattern is **ring fragmentation** into circular aggregates forming a highly regular, periodic array over macroscopic lengths, up to ca. 1mm (Figs. 1-4). The aggregates on the ring are clearly distinct from the localized bright spots generated by the pinholes: In contrast to the latter, the aggregates move in concert with the ring when the position of the source is adjusted. Moreover, in contrast to the spots, the aggregates are *cold*: they do not contain direct excitons (Fig. 4a,b).

The conditions in the ring are optimal for the formation of a very cold exciton gas. The excitons in the ring are formed by electrons and holes which travel over macroscopic distances, and thus may cool to the lattice temperature. This facilitates characterization of the ordered exciton state which appears abruptly as the temperature is decreased below ca. 2K. The phase diagram, obtained from the azimuthal PL distribution Fourier spectrum (Fig. 4c), is presented in Fig. 4d.

The ordered low-temperature exciton phase is a new state that has not been predicted. The temperature dependence (Fig. 4) indicates that exciton ordering is a low temperature phenomenon. Interestingly, it is observed in the same temperature range (below a few Kelvin) as the bosonic stimulation of exciton scattering [15], suggesting that the ordering may be an intrinsic property of a statistically degenerate Bose-gas of excitons. Regarding the relevance of quantum effects, we also note that an estimate of the exciton density in the ring based on the optical shift due to the repulsive dipolar interaction [15] yields $n \sim 10^{10}$ cm^{-2}. This corresponds to the quantum degeneracy temperature $T_0 = (\pi\hbar^2 n)/(2Mgk_B) \sim 0.2$ K, with $M = 0.21\, m_0$ the exciton mass, and $g = 4$ the spin degeneracy of the exciton state in our CQWs, and to the occupation number of the lowest energy state $\nu = e^{T_0/T} - 1 \approx 0.5$ at $T = 0.4$ K [8].

At the onset of quantum degeneracy, the rate at which electrons and holes bind to form excitons will be enhanced due to stimulated processes: $w \propto 1 + \langle\nu\rangle$ in Eq.(1). To see how this can cause a hydrodynamical instability, consider a fluctuation in exciton distribution which leads to growth of exciton density via stimulated electron-hole binding. The depletion of local carrier concentration will cause carriers to stream towards the fluctuation point, attracting more carriers and leading to subsequent increase in exciton density.

The simplest to analyze is instability of a steady state with spatially uniform carrier sources and density distribution. To simplify algebra, we take identical electron and hole parameters in Eqs.(1), $D' = D$, $J'(r) = J(r) = \alpha(n_0 - n)$, with n the electron (also, hole) density. Adding an equation for exciton dynamics,

$$\partial_t n_x = D_x \Delta n_x - \gamma(n_x) + w(n_x) n^2 \qquad (3)$$

with n_x the exciton density, $\gamma(n_x)$ the exciton radiative recombination rate, and linearizing Eqs.(1),(3) over a uniform steady state, we have

$$\begin{pmatrix} \delta\dot{n} - D\Delta\delta n \\ \delta\dot{n}_x - D_x\Delta\delta n_x \end{pmatrix} = -\begin{pmatrix} \lambda + 2wn & w'n^2 \\ -2wn & \gamma' - w'n^2 \end{pmatrix} \begin{pmatrix} \delta n \\ \delta n_x \end{pmatrix}$$

where $w' = dw/dn_x$, $\gamma' = d\gamma/dn_x$. Stability requires a positive definite matrix, which gives $\alpha w' n^2 < (\alpha + 2wn)\gamma'$. Since the binding rate $w(n_x)$ diverges near BEC transition due to the buildup of stimulated processes, the system becomes unstable at temperatures approaching T_{BEC}. The azimuthal modulation wavelength, selected by the competition of the instability with particle diffusion, favors the length scale of the order of the radial exciton distribution width, as seen in experiment.

Besides the outlined scenario, several other mechanisms might account for fragmentation. First, we mention a possibility that exciton dipoles, by tilting spontaneously from the direction normal to CQWs, can reverse the sign of exciton interaction to attractive, causing fragmentation [22]. Also, a purely classical Gann-type effect is possible, in which the radial current distribution becomes nonuniform and develops a modulation in the azimuthal direction. However, the perfect periodicity of the fragments, the phase diagram and, in particular, the low transition temperature, all suggest a fundamental collective mechanism most likely of quantum origin.

Acknowledgements

We thank A.L. Ivanov, L.V. Keldysh, I.V. Kukushkin, D-H Lee, and P.B. Littlewood for valuable discussions. Communications on the theory of PL patterns based on exciton transport and recombination by A.L. Ivanov are greatly appreciated. This work was supported by the Office of Basic Energy Sciences, U.S. Department of Energy under Contract No. DE-AC03-76SF00098 and by RFBR.

LL acknowledges support from "Non-Equilibrium Summer Institute at Los Alamos" and the MRSEC Program of the NSF under Grant No. DMR 98-08941

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FIG. 1. Exciton rings at different photoexcitation intensity. (a-d) The spatial pattern of the indirect exciton PL intensity at $T = 380$ mK, $V_g = 1.24$ V, and $P_{ex} = 310$ (a), 560 (b), and 930 (c,d) μW. On (a-c), the area of view is $410 \times 330\mu$m. (e) Electron, hole, and exciton distribution predicted by the transport model, Eq. (1), at two different excitation intensities. Exciton profile is sharply peaked at the electron-hole interface. (f) CQW band diagram.

FIG. 2. External control of exciton rings. (a-d), Interaction of two exciton rings, the indirect exciton PL pattern at $T = 380$ mK, $V_g = 1.24$ V, and $P_{ex} = 230\mu$W per beam for different separations between the excitation spots. On (a-d), the area of view is $520 \times 240\mu$m. (e-g) Theoretical prediction for the electron-hole interface evolution at decreasing distance between two point sources. Note ring attraction in (b,c,f). (h-j), The indirect exciton spatial PL pattern at $T = 380$mK, $P_{ex} = 1.4$mW for varying gate voltage: $V_g = 1.3$V (h), $V_g = 1.274$V (i), and $V_g = 1.262$V (j), with the area of view $380 \times 320\mu$m.

FIG. 3. Shrinkage of exciton rings to localized bright spots at nearly homogeneous excitation. (a-f) Spatial PL pattern for indirect excitons at $T = 1.8$ K, $V_g = 1.15$ V, and $P_{ex} = 160$ (a), 310 (b), 390 (c), 500 (d), 600 (e), and 1130 (f) μW. On (a-f), the area of view is $690 \times 590\mu$m. The excitation profile along the diagonal for (a-f) is shown in (h). (g) Theoretical electron-hole interface for a point source of holes and a weaker point source of electrons. Arrows show interface displacement at increasing hole number. Note the ring shrinking around electron source. The shrinkage of ring A (d) of indirect excitons is detailed in (i) for $T = 380$ mK, $V_g = 1.155$ V, and $P_{ex} = 77 - 160\mu$W (from left to right) with defocused excitation spot maximum moved to a location directly below ring A. On (i-j), the area of view is $67 \times 67\mu$m for each image. The shrinkage of the rings is accompanied by the onset of the direct exciton emission indicating hot cores at the center of the collapsed rings.

FIG. 4. Fragmented ring and localized spots in the indirect (a) and direct (b) exciton PL image, the area of view is $410 \times 340\mu$m. Note that the hot cores with high-energy direct excitons, present in PL from localized spots, are absent in the ring fragments. (c) Exciton density Fourier transform peak height at the fragmentation period vanishes continuously at a critical temperature. (d) The phase diagram of exciton states in the external ring. The phase boundary of the ordered phase observed at the lowest experimental temperatures (solid line) along with the ring onset region (dashed line) are marked.

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